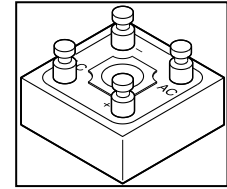


TECHNICAL DATA
DATA SHEET 5121, REV. A

**SINGLE PHASE FULL WAVE
BRIDGE RECTIFIER ASSEMBLY**



DESCRIPTION: A 200/400/600, 9 AMP, 5000 NANOSECOND SINGLE PHASE BRIDGE RECTIFIER ASSEMBLY.

Add suffix "S" for S-100 Screening option.

MAX. RATINGS / ELECTRICAL CHARACTERISTICS All ratings are at $T_A = 25^\circ\text{C}$ unless otherwise specified.

RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV) S10A10 S10A20 S10A40 S10A60 S10A80 S10A100	-	-	-	100 200 400 600 800 1000	Vdc
Average DC Output Current (I_o)	$T_C = 55^\circ\text{C}$ $T_C = 100^\circ\text{C}$	-	-	9 6.75	Amps
Average DC Output Current Ambient Temp. (no heat sink) (I_o)	$T_A = 25^\circ\text{C}$ $T_A = 55^\circ\text{C}$ $T_A = 100^\circ\text{C}$	-	-	3.5 2.5 2.0	Amps
Peak Single Cycle Surge Current (I_{FSM})	$t_p = 8.3$ ms Single Half Cycle Sine Wave	-	-	100	Amps(pk)
Peak Recurring Surge Current (I_{FRM})	$T_C = 25^\circ\text{C}$	-	-	30	Amps
Operating and Storage Temp. (T_{op} & T_{stg})	-	-55	-	+150	$^\circ\text{C}$
Maximum Forward Voltage per leg (V_f)	$I_f = 9.0\text{A}$ (300 μsec pulse, duty cycle < 2%)	-	-	1.40	Volts
Maximum Instantaneous Reverse Current At Rated (PIV)	$T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	-	-	20 200	μAmps
Reverse Recovery Time (t_{rr})	$I_f = 0.5\text{A}$, $I_r = 1.0\text{A}$, $I_{rr} =$ 0.25A	-	-	5000	nsec
Thermal Resistance (θ_{JC})	-	-	-	2.0	$^\circ\text{C/W}$

TECHNICAL DATA
DATA SHEET 5121, REV. A

MECHANICAL DIMENSIONS: In Inches / mm

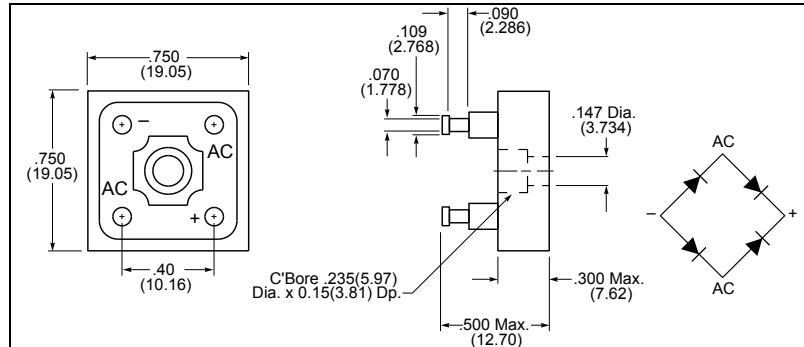


FIG. 401

Note: Case finish - Black Anodized

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